

# NUD3105D

## Integrated Relay, Inductive Load Driver

This device is used to switch inductive loads such as relays, solenoids incandescent lamps, and small DC motors without the need of a free-wheeling diode. The device integrates all necessary items such as the MOSFET switch, ESD protection, and Zener clamps. It accepts logic level inputs thus allowing it to be driven by a large variety of devices including logic gates, inverters, and microcontrollers.

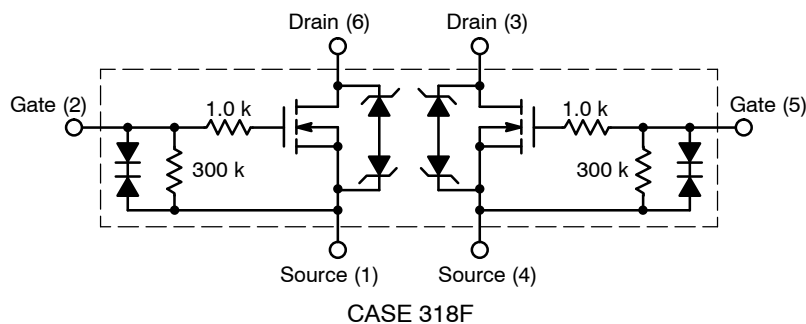
### Features

- Provides a Robust Driver Interface Between D.C. Relay Coil and Sensitive Logic Circuits
- Optimized to Switch Relays from 3.0 V to 5.0 V Rail
- Capable of Driving Relay Coils Rated up to 2.5 W at 5.0 V
- Internal Zener Eliminates the Need of Free-Wheeling Diode
- Internal Zener Clamp Routes Induced Current to Ground for Quieter Systems Operation
- Low  $V_{DS(on)}$  Reduces System Current Drain
- Pb-Free Package is Available

### Typical Applications

- Telecom: Line Cards, Modems, Answering Machines, FAX
- Computers and Office: Photocopiers, Printers, Desktop Computers
- Consumer: TVs and VCRs, Stereo Receivers, CD Players, Cassette Recorders
- Industrial: Small Appliances, Security Systems, Automated Test Equipment, Garage Door Openers
- Automotive: 5.0 V Driven Relays, Motor Controls, Power Latches, Lamp Drivers

### INTERNAL CIRCUIT DIAGRAMS



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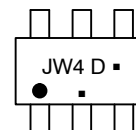
<http://onsemi.com>

## Relay, Inductive Load Driver 0.5 Amp, 8.0 V Clamp

### MARKING DIAGRAM



**SC-74  
CASE 318F  
STYLE 7**



JW4 = Specific Device Code  
D = Date Code  
▪ = Pb-Free Package

(Note: Microdot may be in either location)

### ORDERING INFORMATION

Device	Package	Shipping†
NUD3105DMT1	SC-74	3000/Tape & Reel
NUD3105DMT1G	SC-74 (Pb-Free)	3000/Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

# NUD3105D

## MAXIMUM RATINGS ( $T_J = 25^\circ\text{C}$ unless otherwise specified)

Symbol	Rating	Value	Unit
$V_{DSS}$	Drain to Source Voltage – Continuous	6.0	$V_{dc}$
$V_{GS}$	Gate to Source Voltage – Continuous	6.0	$V_{dc}$
$I_D$	Drain Current – Continuous	500	mA
$E_z$	Single Pulse Drain-to-Source Avalanche Energy ( $T_{Jinitial} = 25^\circ\text{C}$ )	50	mJ
$T_J$	Junction Temperature	150	$^\circ\text{C}$
$T_A$	Operating Ambient Temperature	-40 to 85	$^\circ\text{C}$
$T_{stg}$	Storage Temperature Range	-65 to +150	$^\circ\text{C}$
$P_D$	Total Power Dissipation (Note 1) Derating Above $25^\circ\text{C}$	380 1.5	mW mW/ $^\circ\text{C}$
$R_{\theta JA}$	Thermal Resistance Junction-to-Ambient	329	$^\circ\text{C}/\text{W}$

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

- This device contains ESD protection and exceeds the following tests:  
Human Body Model 2000 V per MIL\_STD-883, Method 3015.  
Machine Model Method 200 V.

## TYPICAL ELECTRICAL CHARACTERISTICS ( $T_J = 25^\circ\text{C}$ unless otherwise noted)

Symbol	Characteristic	Min	Typ	Max	Unit
<b>OFF CHARACTERISTICS</b>					
$V_{BRDSS}$	Drain to Source Sustaining Voltage (Internally Clamped) ( $I_D = 10\text{ mA}$ )	6.0	8.0	9.0	V
$B_{VGS0}$	$I_g = 1.0\text{ mA}$	–	–	8.0	V
$I_{DSS}$	Drain to Source Leakage Current ( $V_{DS} = 5.5\text{ V}$ , $V_{GS} = 0\text{ V}$ , $T_J = 25^\circ\text{C}$ ) ( $V_{DS} = 5.5\text{ V}$ , $V_{GS} = 0\text{ V}$ , $T_J = 85^\circ\text{C}$ )	– –	– –	15 15	$\mu\text{A}$
$I_{GSS}$	Gate Body Leakage Current ( $V_{GS} = 3.0\text{ V}$ , $V_{DS} = 0\text{ V}$ ) ( $V_{GS} = 5.0\text{ V}$ , $V_{DS} = 0\text{ V}$ )	5.0 –	– –	35 65	$\mu\text{A}$
<b>ON CHARACTERISTICS</b>					
$V_{GS(th)}$	Gate Threshold Voltage ( $V_{GS} = V_{DS}$ , $I_D = 1.0\text{ mA}$ ) ( $V_{GS} = V_{DS}$ , $I_D = 1.0\text{ mA}$ , $T_J = 85^\circ\text{C}$ )	0.8 0.8	1.2 –	1.4 1.4	V
$R_{DS(on)}$	Drain to Source On-Resistance ( $I_D = 250\text{ mA}$ , $V_{GS} = 3.0\text{ V}$ ) ( $I_D = 500\text{ mA}$ , $V_{GS} = 3.0\text{ V}$ ) ( $I_D = 500\text{ mA}$ , $V_{GS} = 5.0\text{ V}$ ) ( $I_D = 500\text{ mA}$ , $V_{GS} = 3.0\text{ V}$ , $T_J = 85^\circ\text{C}$ ) ( $I_D = 500\text{ mA}$ , $V_{GS} = 5.0\text{ V}$ , $T_J = 85^\circ\text{C}$ )	– – – – –	– – – – –	1.2 1.3 0.9 1.3 0.9	$\Omega$
$I_{DS(on)}$	Output Continuous Current ( $V_{DS} = 0.25\text{ V}$ , $V_{GS} = 3.0\text{ V}$ ) ( $V_{DS} = 0.25\text{ V}$ , $V_{GS} = 3.0\text{ V}$ , $T_J = 85^\circ\text{C}$ )	300 200	400 –	– –	mA
$g_{FS}$	Forward Transconductance ( $V_{OUT} = 5.0\text{ V}$ , $I_{OUT} = 0.25\text{ A}$ )	350	570	–	mMhos

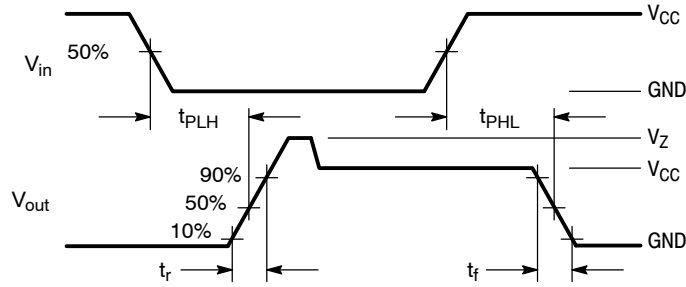
# NUD3105D

## TYPICAL ELECTRICAL CHARACTERISTICS ( $T_J = 25^\circ\text{C}$ unless otherwise noted)

Symbol	Characteristic	Min	Typ	Max	Unit
<b>DYNAMIC CHARACTERISTICS</b>					
$C_{iss}$	Input Capacitance ( $V_{DS} = 5.0\text{ V}, V_{GS} = 0\text{ V}, f = 10\text{ kHz}$ )	-	25	-	pF
$C_{oss}$	Output Capacitance ( $V_{DS} = 5.0\text{ V}, V_{GS} = 0\text{ V}, f = 10\text{ kHz}$ )	-	37	-	pF
$C_{rss}$	Transfer Capacitance ( $V_{DS} = 5.0\text{ V}, V_{GS} = 0\text{ V}, f = 10\text{ kHz}$ )	-	8.0	-	pF

## SWITCHING CHARACTERISTICS

Symbol	Characteristic	Min	Typ	Max	Units
$t_{PHL}$ $t_{PLH}$	Propagation Delay Times: High to Low Propagation Delay; Figure 1 (5.0 V) Low to High Propagation Delay; Figure 1 (5.0 V)	-	25 80	-	nS
$t_{PHL}$ $t_{PLH}$	High to Low Propagation Delay; Figure 1 (3.0 V) Low to High Propagation Delay; Figure 1 (3.0 V)	-	44 44	-	nS
$t_f$ $t_r$	Transition Times: Fall Time; Figure 1 (5.0 V) Rise Time; Figure 1 (5.0 V)	-	23 32	-	nS
$t_f$ $t_r$	Fall Time; Figure 1 (3.0 V) Rise Time; Figure 1 (3.0 V)	-	53 30	-	-



**Figure 1. Switching Waveforms**

TYPICAL CHARACTERISTICS

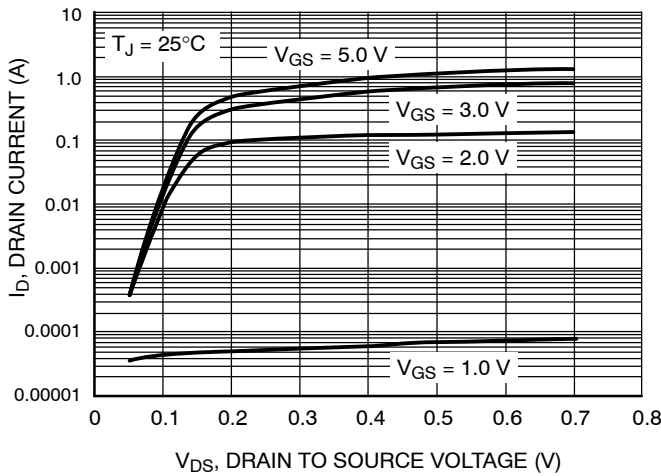


Figure 2. Output Characteristics

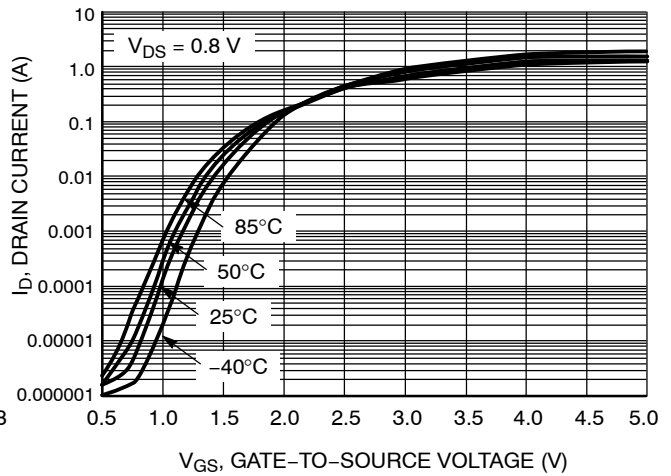


Figure 3. Transfer Function

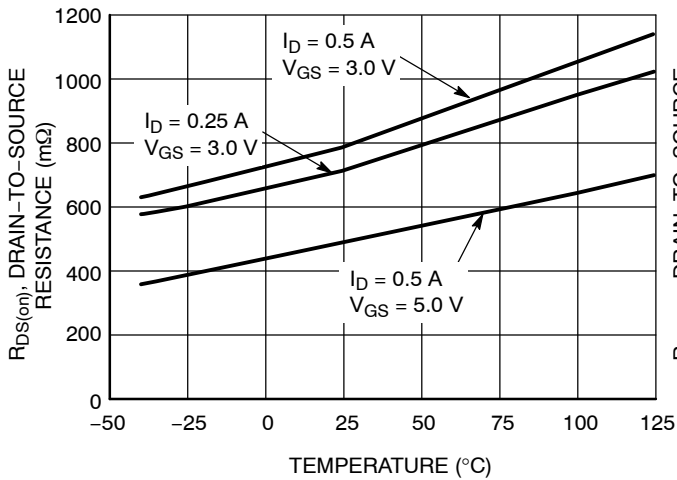


Figure 4. On Resistance Variation vs. Temperature

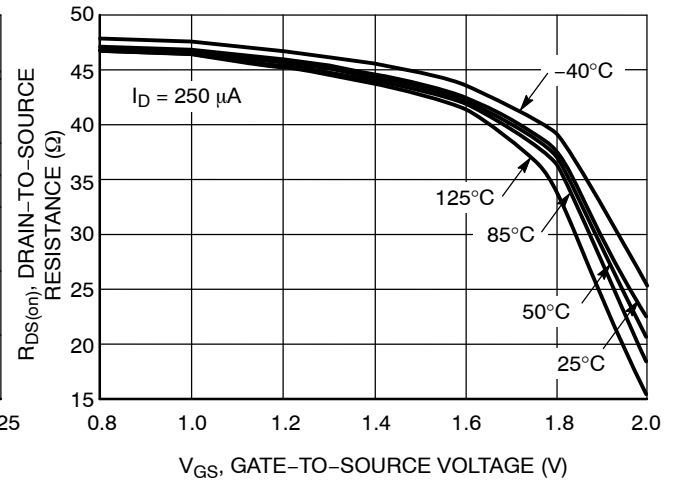


Figure 5.  $R_{DS(ON)}$  Variation with Gate-to-Source Voltage

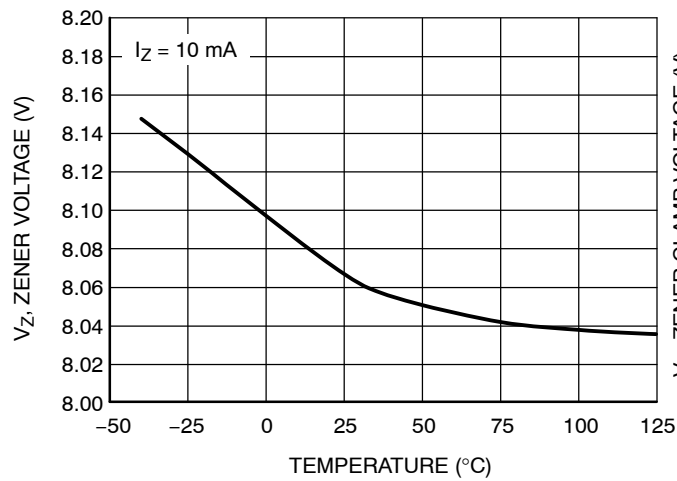


Figure 6. Zener Voltage vs. Temperature

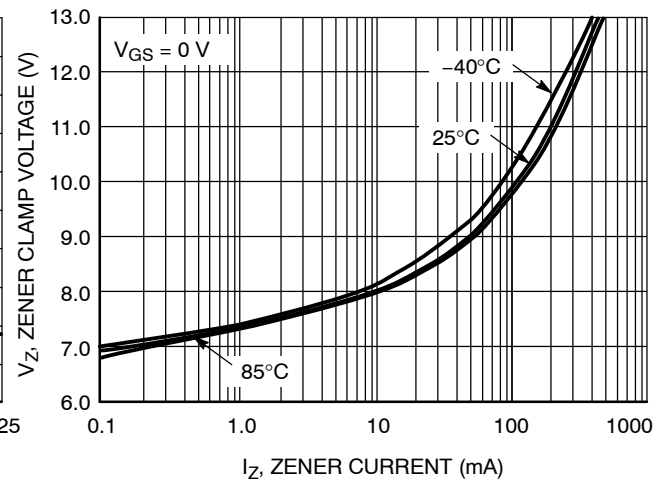


Figure 7. Zener Clamp Voltage vs. Zener Current

# NUD3105D

## TYPICAL CHARACTERISTICS

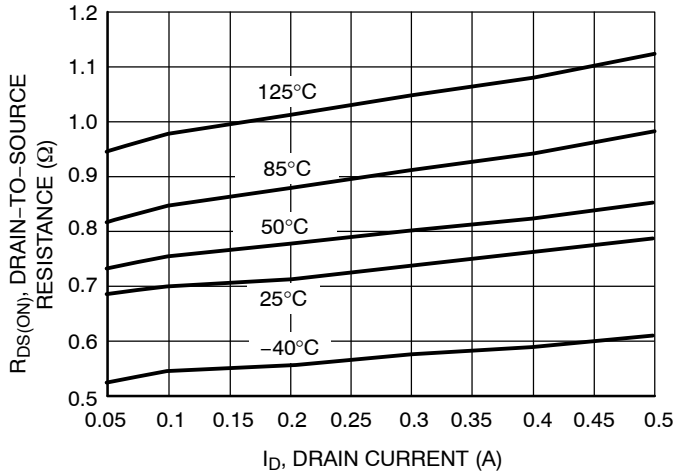


Figure 8. On-Resistance vs. Drain Current and Temperature

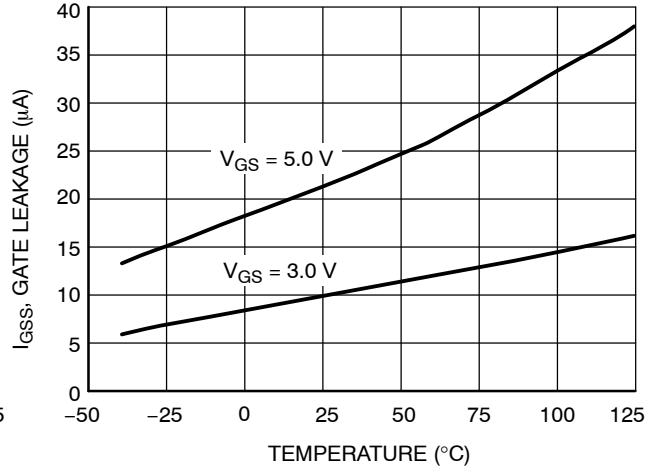


Figure 9. Gate Leakage vs. Temperature

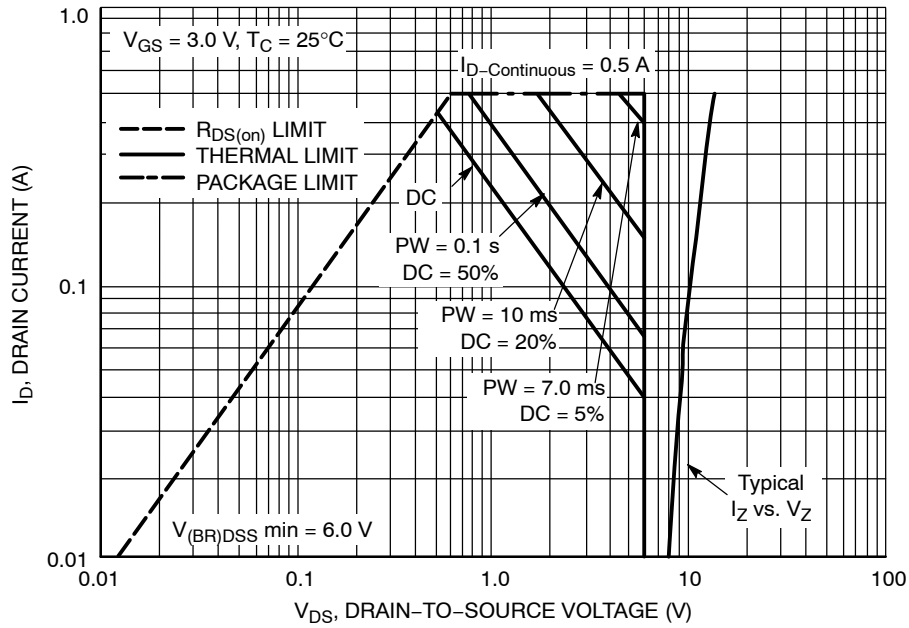


Figure 10. Safe Operating Area for NUD3105DLT1

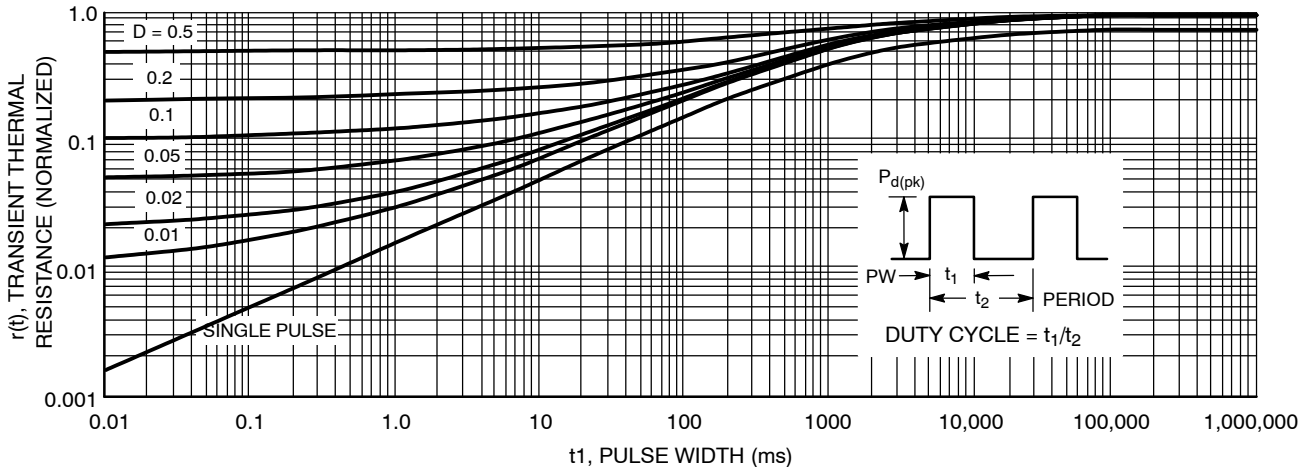


Figure 11. Transient Thermal Response for NUD3105DLT1

# NUD3105D

## Designing with this Data Sheet

1. Determine the maximum inductive load current (at max  $V_{CC}$ , min coil resistance & usually minimum temperature) that the NUD3105D will have to drive and make sure it is less than the max rated current.
2. For pulsed operation, use the Transient Thermal Response of Figure 11 and the instructions with it to determine the maximum limit on transistor power dissipation for the desired duty cycle and temperature range.
3. Use Figures 10 and 11 with the SOA notes to insure that instantaneous operation does not push the device beyond the limits of the SOA plot.
4. Verify that the circuit driving the gate will meet the  $V_{GS(th)}$  from the Electrical Characteristics table.
5. Using the max output current calculated in step 1, check Figure 7 to insure that the range of Zener clamp voltage over temperature will satisfy all system & EMI requirements.
6. Use  $I_{GSS}$  and  $I_{DSS}$  from the Electrical Characteristics table to insure that "OFF" state leakage over temperature and voltage extremes does not violate any system requirements.
7. Review circuit operation and insure none of the device max ratings are being exceeded.

## APPLICATIONS DIAGRAMS

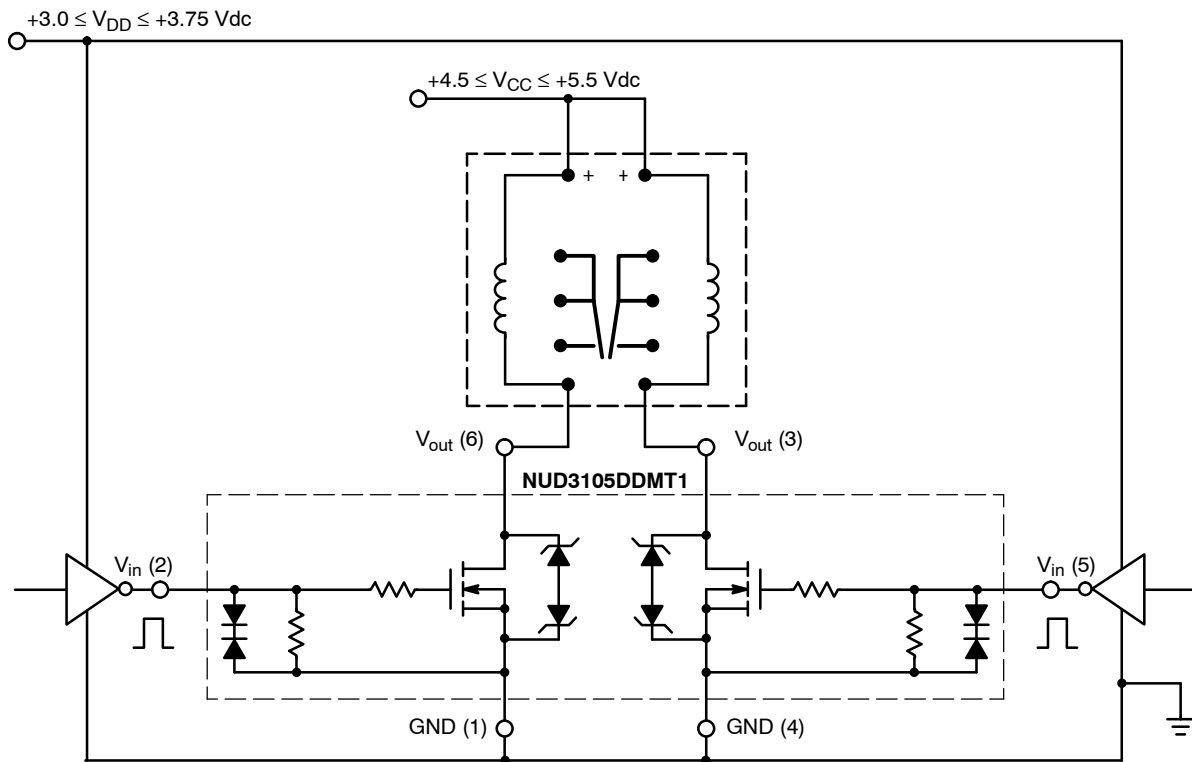


Figure 12. A 200 mW, 5.0 V Dual Coil Latching Relay Application with 3.0 V Level Translating Interface

# NUD3105D

## Max Continuous Current Calculation

for TX2-5V Relay,  $R_1 = 178 \Omega$  Nominal @  $R_A = 25^\circ\text{C}$

Assuming  $\pm 10\%$  Make Tolerance,

$R_1 = 178 \Omega * 0.9 = 160 \Omega$  Min @  $T_A = 25^\circ\text{C}$

$T_C$  for Annealed Copper Wire is  $0.4\%/^\circ\text{C}$

$R_1 = 160 \Omega * [1 + (0.004) * (-40^\circ - 25^\circ)] = 118 \Omega$  Min @  $-40^\circ\text{C}$

$I_O \text{ Max} = (5.5 \text{ V Max} - 0.25\text{V}) / 118 \Omega = 45 \text{ mA}$

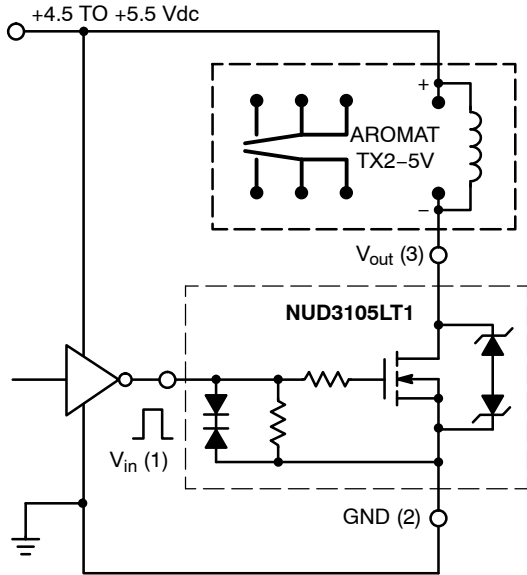


Figure 13. A 140 mW, 5.0 V Relay with TTL Interface

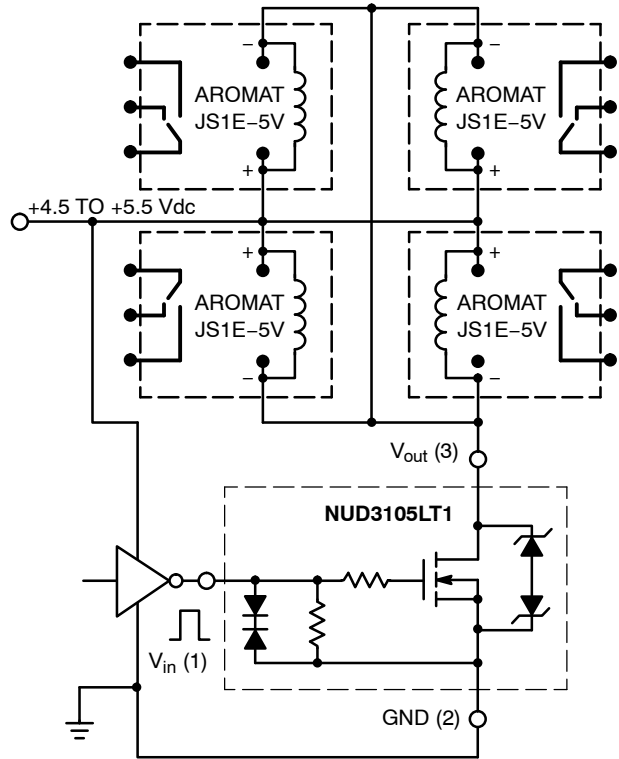


Figure 14. A Quad 5.0 V, 360 mW Coil Relay Bank

# MECHANICAL CASE OUTLINE

## PACKAGE DIMENSIONS

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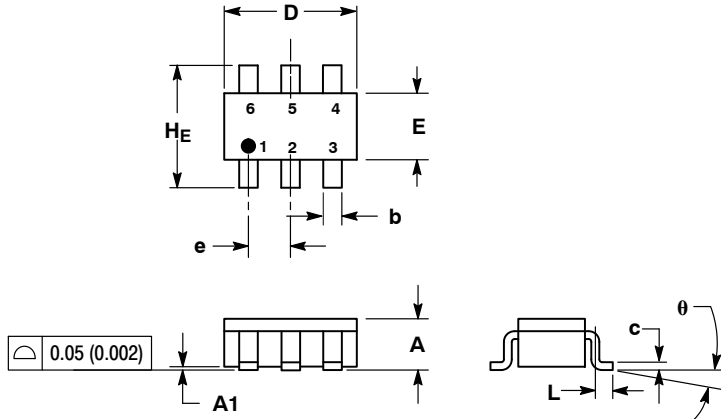
### SC-74

#### CASE 318F-05

#### ISSUE N

DATE 08 JUN 2012

SCALE 2:1

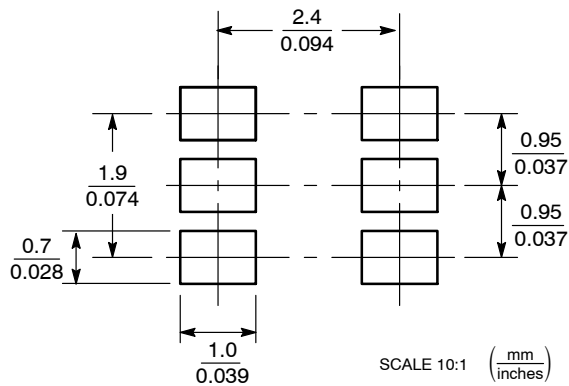


NOTES:

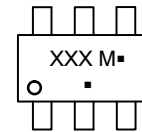
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. 318F-01, -02, -03, -04 OBSOLETE. NEW STANDARD 318F-05.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.90	1.00	1.10	0.035	0.039	0.043
A1	0.01	0.06	0.10	0.001	0.002	0.004
b	0.25	0.37	0.50	0.010	0.015	0.020
c	0.10	0.18	0.26	0.004	0.007	0.010
D	2.90	3.00	3.10	0.114	0.118	0.122
E	1.30	1.50	1.70	0.051	0.059	0.067
e	0.85	0.95	1.05	0.034	0.037	0.041
L	0.20	0.40	0.60	0.008	0.016	0.024
HE	2.50	2.75	3.00	0.099	0.108	0.118
θ	0°	-	10°	0°	-	10°

#### SOLDERING FOOTPRINT\*



#### GENERIC MARKING DIAGRAM\*



- XXX = Specific Device Code
- M = Date Code
- = Pb-Free Package

(Note: Microdot may be in either location)

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present.

\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

- |   |  |   |  |   |   |
|---|--|---|--|---|---|
| <p>STYLE 1:<br/>PIN 1. CATHODE<br/>2. ANODE<br/>3. CATHODE<br/>4. CATHODE<br/>5. ANODE<br/>6. CATHODE</p>     | <p>STYLE 2:<br/>PIN 1. NO CONNECTION<br/>2. COLLECTOR<br/>3. EMITTER<br/>4. NO CONNECTION<br/>5. COLLECTOR<br/>6. BASE</p> | <p>STYLE 3:<br/>PIN 1. EMITTER 1<br/>2. BASE 1<br/>3. COLLECTOR 2<br/>4. EMITTER 2<br/>5. BASE 2<br/>6. COLLECTOR 1</p> | <p>STYLE 4:<br/>PIN 1. COLLECTOR 2<br/>2. EMITTER 1/EMITTER 2<br/>3. COLLECTOR 1<br/>4. EMITTER 3<br/>5. BASE 1/BASE 2/COLLECTOR 3<br/>6. BASE 3</p> | <p>STYLE 5:<br/>PIN 1. CHANNEL 1<br/>2. ANODE<br/>3. CHANNEL 2<br/>4. CHANNEL 3<br/>5. CATHODE<br/>6. CHANNEL 4</p> | <p>STYLE 6:<br/>PIN 1. CATHODE<br/>2. ANODE<br/>3. CATHODE<br/>4. CATHODE<br/>5. CATHODE<br/>6. CATHODE</p> |
| <p>STYLE 7:<br/>PIN 1. SOURCE 1<br/>2. GATE 1<br/>3. DRAIN 2<br/>4. SOURCE 2<br/>5. GATE 2<br/>6. DRAIN 1</p> | <p>STYLE 8:<br/>PIN 1. EMITTER 1<br/>2. BASE 2<br/>3. COLLECTOR 2<br/>4. EMITTER 2<br/>5. BASE 1<br/>6. COLLECTOR 1</p>    | <p>STYLE 9:<br/>PIN 1. EMITTER 2<br/>2. BASE 2<br/>3. COLLECTOR 1<br/>4. EMITTER 1<br/>5. BASE 1<br/>6. COLLECTOR 2</p> | <p>STYLE 10:<br/>PIN 1. ANODE/CATHODE<br/>2. BASE<br/>3. EMITTER<br/>4. COLLECTOR<br/>5. ANODE<br/>6. CATHODE</p>                                    | <p>STYLE 11:<br/>PIN 1. EMITTER<br/>2. BASE<br/>3. ANODE/CATHODE<br/>4. ANODE<br/>5. CATHODE<br/>6. COLLECTOR</p>   |   |

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